U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Application No.
	NS-5127 US	10/054,653
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	Confirmation No.
Substitute PTO Form 1449	Constantin Bulucea	9448
	Filing Date	Group
	January 18, 2002	2814

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	AL							
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	AN							
	AO							
	AP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

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Examiner	Date Considered 9/30/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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